



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

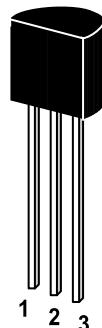
ST 2SC1008

NPN Silicon Epitaxial Planar Transistor

for medium speed switching and low frequency
amplifier applications.

The transistor is subdivided into three groups, R, O,
Y, and G according to its DC current gain.

On special request, these transistors can be
manufactured in different pin configurations.

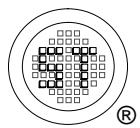


1. Emitter 2. Base 3. Collector

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	700	mA
Collector Power Dissipation	P_{tot}	800	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	-55 to +150	°C



Dated : 7/12/2002



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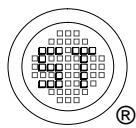
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Characteristics at $T_{amb}=25^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE}=2\text{V}$, $I_C=50\text{mA}$	R O Y G	h_{FE} h_{FE} h_{FE} h_{FE}	40 70 120 200	- - - -	80 140 240 400	- - - -
Collector Saturation Voltage at $I_C=500\text{mA}$, $I_B=50\text{mA}$		V_{CESat}	-	0.2	0.4	V
Base Saturation Voltage at $I_C=500\text{mA}$, $I_B=50\text{mA}$		V_{BESat}	-	0.86	1.1	V
Collector Base Breakdown Voltage at $I_C=100\mu\text{A}$, $I_E=0$		BV_{CBO}	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C=10\text{mA}$, $I_B=0$		BV_{CEO}	40	-	-	V
Emitter Base Breakdown Voltage at $I_E=10\mu\text{A}$, $I_C=0$		BV_{EBO}	6	-	-	V
Collector Cut-off Current at $V_{CB}=60\text{V}$, $I_E=0$		I_{CBO}	-	-	0.1	μA
Emitter Cut-off Current at $V_{EB}=5\text{V}$, $I_C=0$		I_{EBO}	-	-	0.1	μA
Gain Bandwidth Product at $V_{CE}=10\text{V}$, $I_C=50\text{mA}$		f_T	30	50	-	MHz
Output Capacitance at $V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$		C_{ob}	-	8	-	pF



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